



DOCUMENT CHANGE REQUEST

DCR number 670 Changes required for: General

Date: 2011/09/29

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Status: IMPLEMENTED

Originator: Steve Jeffery

Organisation: ESCC Executive Secretariat

Title: Transistors, Power, MOSFET, N-Channel, RAD-HARD, based on Type STRH100N10FSY3

Number: 5205/021

Issue: 2

Other documents affected:

Page:

Paragraph:

Original wording:

Page 1 / Page 5, Para. 1.4.2 / Page 17, Appendix 'A' Additional Data – STMicroelectronics (F)

Proposed wording:

Page 1, Based on Type and Page 5, Para. 1.4.2: delete suffix FSY3 from the "Based on Type".

Page 17, Additional Data - STMicroelectronics (F), (a) Derating for Space Application has been revised as follows:

- The original wording "... Single Event Gate Rupture when operated in a space environment unless the following derating is applied during their use:", is to be replaced by "... Single Event Gate Rupture if operated in a space environment unless the following derating is applied. The derating for space applications was originally obtained on STRH100N10 devices under the following test conditions. The testing was performed in a vacuum at UCL (Louvain-la-Neuve, Belgium):"
- The text "NOTES: 1. The derating for space application information was originally obtained under the following test conditions:" is to be deleted.
- The test conditions [Ion used / LET / Energy / Range] shall be re-positioned above the derating information (due to the first revision above).
- The LET was "32MeV / (mg/cm²)" but should be "32 (MeV / (mg/cm²))".

Justification:

The proposed editorial changes to the ESCC Detail Specification, described above, supplement the proposed changes described in DCR 654 and will homogenise the format and content of 5205/021 Issue 3 with that of the recently-published ESCC Detail Specifications 5205/022 Issue 1 (Based on Type STRH100N6), 5205/023 Issue 1 (Based on Type STRH8N10), 5205/024 Issue 1 (Based on Type STRH40N6) and 5205/025 Issue 1 (Based on Type STRH40P10).

Attachments:
N/A
Modifications:
N/A
Approval signature:

Date signed:
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